

# isc Silicon PNP Power Transistor

# 2SB1186

#### **DESCRIPTION**

- High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -120V(Min.)
- · Good Linearity of hFE
- Complement to Type 2SD1763
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

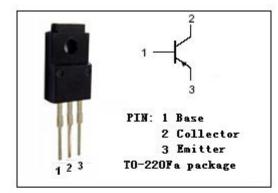
#### **APPLICATIONS**

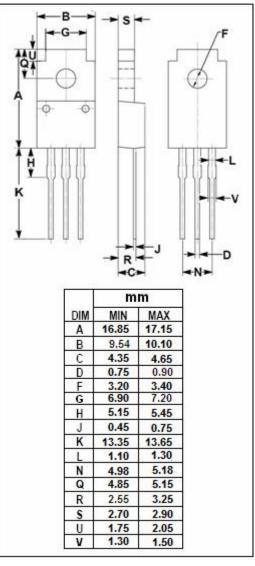


- · Power amplifier applications.
- Driver stage amplifier applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-120	V	
V <sub>CEO</sub>	Collector-Emitter Voltage -120		V	
V <sub>EBO</sub>	Emitter-Base Voltage -5		V	
Ic	Collector Current-Continuous	А		
Ісм	Collector Current-Peak	ollector Current-Peak -3 A		
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	10/	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	20	W	
TJ	Junction Temperature 150		°C	
T <sub>stg</sub>	Storage Temperature Range -55~150		°C	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -50 μ <b>A</b> ; I <sub>E</sub> = 0	-120			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -50 μ A; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -0.1A			-2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -0.1A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-1	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-1	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.1A; V <sub>CE</sub> = -5V	100		320	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> =1MHz		30		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = 0.1A; V <sub>CE</sub> = -5V; f <sub>test</sub> = 30MHz		50		MHz

## ♦ h<sub>FE</sub> Classifications

E	F			
100-200	160-320			

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